

 Saved

31 and 27

Nov 2004

| | U | T | Inventor | Document | Issue | P | Title | Current | Current XA | Retrieval | S | C | P | T | Image | Doc. | P |
|----|---|---|---------------|------------|-------|---|--|---------|------------|-----------|---|---|---|---|-------|------|------------|
| 1 | | | Lee, Jung Ho | US 6768158 | 20040 | 1 | Flash memory element and manufacturing me | 257/315 | 257/317 | | R | F | F | R | F | F | US 6768158 |
| 2 | | | Fried, David | US 6750487 | 20040 | 1 | Dual double gate transistor | 257/270 | 257/206 | | R | F | F | F | F | F | US 6750487 |
| 3 | | | Yeo, Yee-Chia | US 2004011 | 20040 | 1 | CMOS inverters configured using multiple-ga | 438/199 | | | R | F | F | F | F | F | US 2004011 |
| 4 | | | Chen, Hao-Yu | US 2004010 | 20040 | 1 | Multiple-gate transistor structure and metho | 257/202 | | | R | F | F | F | F | F | US 2004011 |
| 5 | | | Krivokapic, Z | US 2004010 | 20040 | 1 | Two transistor nor device | 326/112 | 257/E27.06 | | R | F | F | F | F | F | US 2004011 |
| 6 | | | Yeo, Yee-Chia | US 2004009 | 20040 | 1 | Strained channel multiple-gate transistor | 257/317 | | | R | F | F | F | F | F | US 2004009 |
| 7 | | | Fried, David | US 2003019 | 20031 | 1 | FIN MEMORY CELL AND METHOD OF FABRI | 257/200 | | | R | F | F | F | F | F | US 2003019 |
| 8 | | | Fried, David | US 2003019 | 20031 | 1 | Dual double gate transistor and method for f | 257/328 | 257/331 | | R | F | F | F | F | F | US 2003019 |
| 9 | | | Fischetti, Ma | US 2003019 | 20031 | 1 | Germanium field effect transistor and metho | 438/305 | 257/E21.63 | | R | F | F | F | F | F | US 2003019 |
| 10 | | | Fried, David | US 2003014 | 20030 | 1 | Fin-type resistors | 257/536 | 257/379 | | R | F | F | F | F | F | US 2003014 |